

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro SAKURADA et al.

Application No.: New U.S. Patent Application

Filed: June 14, 2005

Docket No.: 124231

For: METHOD OF PRODUCING P-DOPED SILICON SINGLE CRYSTAL AND P-DOPED
N-TYPE SILICON SINGLE CRYSTAL WAFER

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please consider the following:

Amendments to the Specification;

Amendments to the Claims as reflected in the listing of claims; and

Remarks.